

ABSTRACT

A polishing slurry for metal comprises an oxidizer, a metal oxide dissolving agent, a metal inhibitor, and water, wherein the metal inhibitor is at least one of a compound having an amino-triazole skeleton and a compound having an imidazole skeleton. The use of the polishing slurry for metal makes it possible to raise the polishing speed sufficiently while keeping the etching speed low, restrain the generation of corrosion of the surface of a metal and dishing, and form a metal-film-buried pattern having a high reliability in the process of formation of wiring of semiconductor devices.